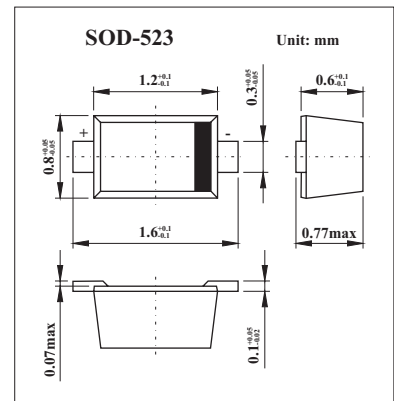


## Silicon Epitaxial Planar Pin Diode

## HVC131



### ■ Features

- Low capacitance. (C=0.8pF max)
- Low forward resistance. ( $r_f=1.0\ \Omega$  max)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}$	65	V
Reverse voltage	$V_R$	60	V
Forward current	$I_F$	100	mA
Power dissipation	$P_d$	150	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	$I_R$	$V_R = 60\ \text{V}$			0.1	$\mu\text{A}$
Reverse voltage	$V_F$	$I_F = 10\ \text{mA}$			1.0	V
Capacitance	C	$V_R = 1\ \text{V}, f = 1\ \text{MHz}$			0.8	pF
Forward resistance	$r_f$	$I_F = 10\ \text{mA}, f = 100\ \text{MHz}$			1.0	$\Omega$

### ■ Marking

Marking	P1
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